



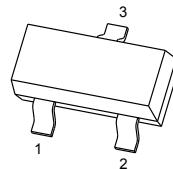
DONGGUAN NANJING ELECTRONICS LTD.,

SOT-23 Plastic-Encapsulate MOSFETs

2N7002 MOSFET (N-Channel)

$V_{(BR)DSS}$	$R_{DS(on)}\text{MAX}$	I_D
60 V	2.5Ω@10V	115mA
	3Ω@5V	

SOT-23



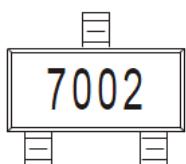
FEATURE

- High density cell design for low $R_{DS(\text{ON})}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

APPLICATION

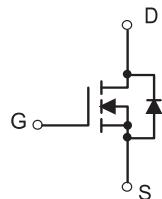
- Load Switch for Portable Devices
- DC/DC Converter

MARKING



7002=Device code

Equivalent Circuit



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	0.115	A
Power Dissipation	P_D	0.225	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	556	°C/W
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-50 ~+150	°C

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^\circ\text{C}$ unless otherwise specified

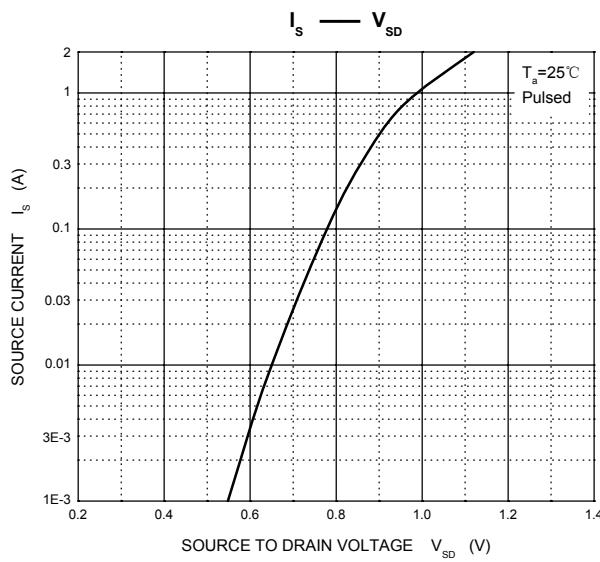
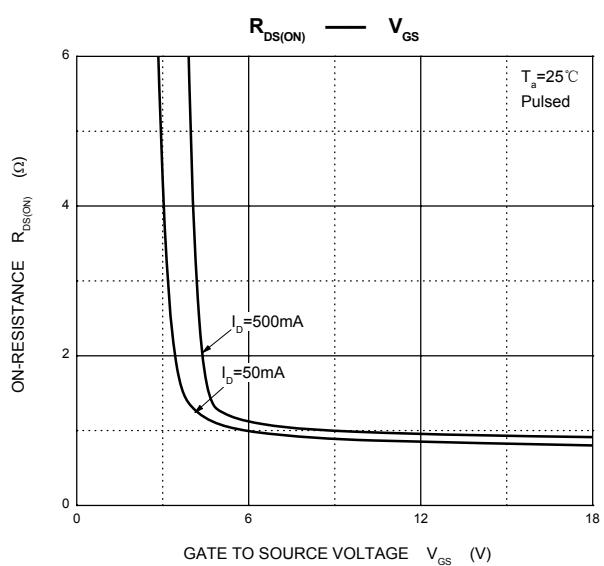
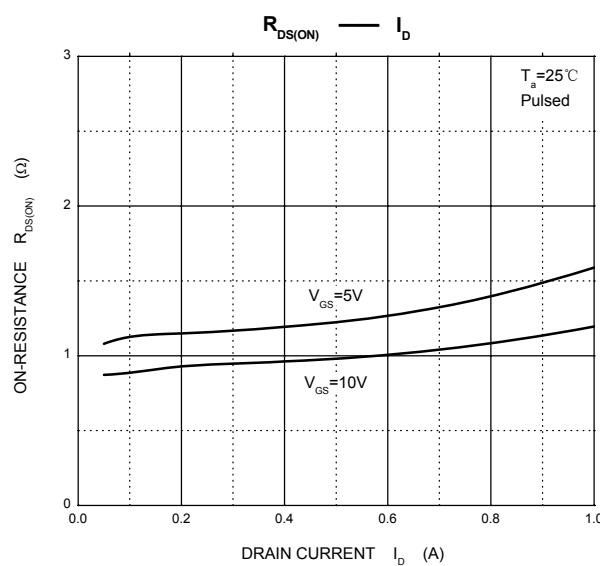
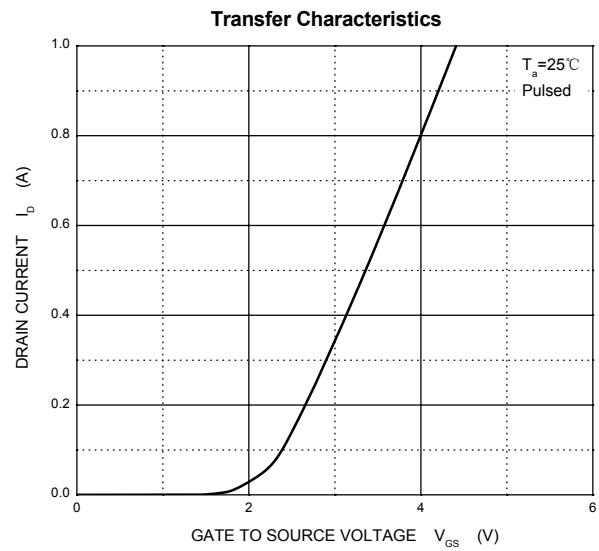
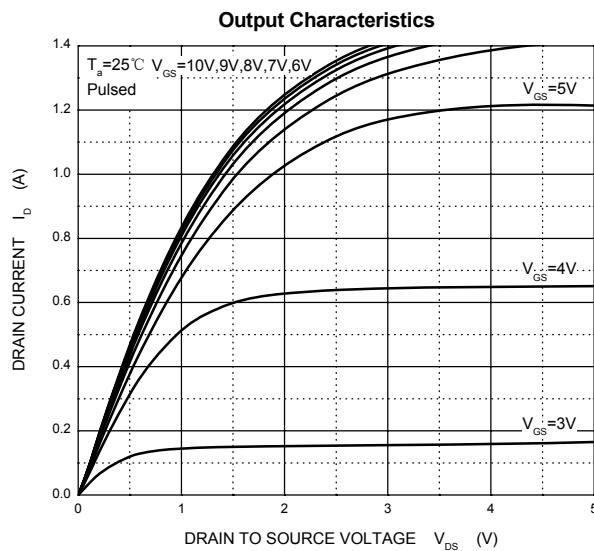
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}}=0 \text{ V}, I_D=250 \mu\text{A}$	60			V
Gate-Threshold Voltage	$V_{\text{th}(\text{GS})}$	$V_{\text{DS}}=V_{\text{GS}}, I_D=250 \mu\text{A}$	1	1.6	2.5	
Gate-body Leakage	I_{GSS}	$V_{\text{DS}}=0 \text{ V}, V_{\text{GS}}=\pm 20 \text{ V}$			± 80	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=60 \text{ V}, V_{\text{GS}}=0 \text{ V}$			80	nA
On-state Drain Current	$I_{\text{D}(\text{ON})}$	$V_{\text{GS}}=10 \text{ V}, V_{\text{DS}}=7 \text{ V}$	500			mA
Drain-Source On-Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=10 \text{ V}, I_D=500 \text{ mA}$		0.9	2.5	Ω
		$V_{\text{GS}}=5 \text{ V}, I_D=50 \text{ mA}$		1.1	3	
Forward Trans conductance	g_{fs}	$V_{\text{DS}}=10 \text{ V}, I_D=200 \text{ mA}$	80			ms
Drain-source on-voltage	$V_{\text{DS}(\text{on})}$	$V_{\text{GS}}=10 \text{ V}, I_D=500 \text{ mA}$			3.75	V
		$V_{\text{GS}}=5 \text{ V}, I_D=50 \text{ mA}$			0.375	V
Diode Forward Voltage	V_{SD}	$I_S=115 \text{ mA}, V_{\text{GS}}=0 \text{ V}$	0.55		1.2	V
Input Capacitance *	C_{iss}	$V_{\text{DS}}=25 \text{ V}, V_{\text{GS}}=0 \text{ V}, f=1 \text{ MHz}$			50	pF
Output Capacitance *	C_{oss}				25	
Reverse Transfer Capacitance *	C_{rss}				5	

SWITCHING TIME

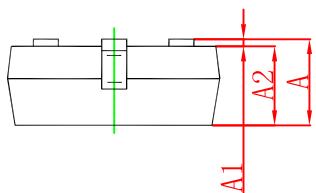
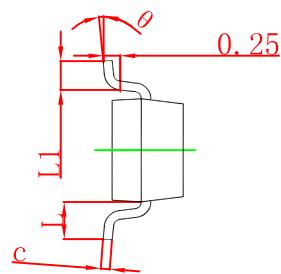
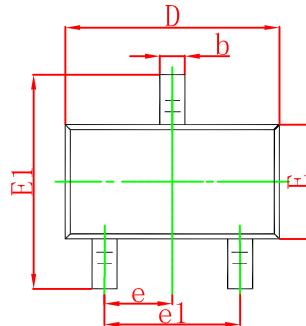
Turn-on Time *	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=25 \text{ V}, R_L=50 \Omega, I_D=500 \text{ mA}, V_{\text{GEN}}=10 \text{ V}$			20	ns
Turn-off Time *	$t_{\text{d}(\text{off})}$	$R_G=25 \Omega$			40	

*These parameters have no way to verify.

Typical Characteristics

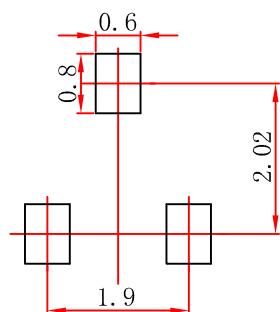


SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout

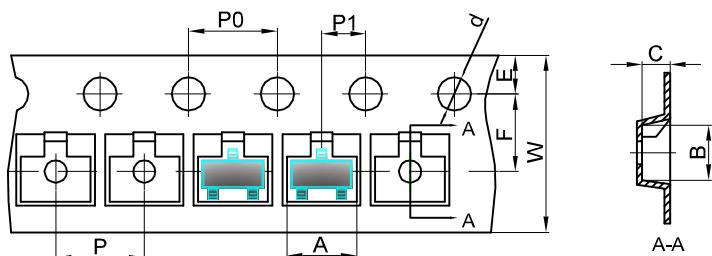


Note:

1. Controlling dimension:in millimeters.
- 2.General tolerance: $\pm 0.05\text{mm}$.
- 3.The pad layout is for reference purposes only.

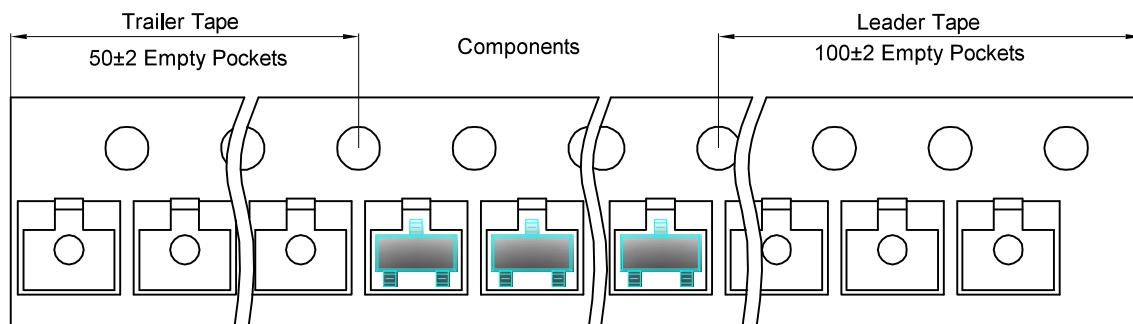
SOT-23 Tape and reel

SOT-23 Embossed Carrier Tape

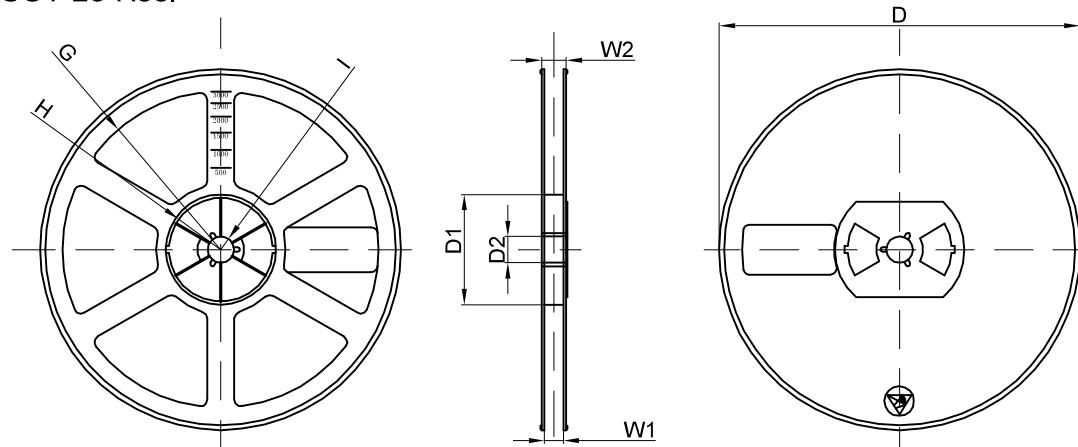


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	